NSN 5961-01-230-5914

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-230-5914 **Inclosure Material:** Metal **Overall Length:** 0.180 inches **Terminal Length:** 1.500 inches **Overall Diameter:** 0.370 inches **End Application:** Group programmer **Component Name And Quantity:** 2 transistor **Mounting Method: Terminal Semiconductor Material:** Silicon all transistor **Voltage Rating In Volts Per Characteristic:** 75.0 collector to base voltage/static/emitter open all transistor and 40.0 collector to emitter voltage/static/base open all transistor and 6.0 emitter to base voltage, static, collector open all transistor **Current Rating Per Characteristic:** 600.00 milliamperes source cutoff current all transistor **Power Rating Per Characteristic:** 500.0 milliwatts small-signal input power, common-collector all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** All transistor junction pattern arrangement: npn **Nuclear Hardness Critical Feature:** Hardened **Test Data Document:** 81205-bacs8a drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 6 uninsulated wire lead Shelf Life: N/a **Unit Of Measure:**

Fiig:

A110a0

Demilitarization: Yes - demil/mli